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# FCD600N60Z

## N-Channel SuperFET® II MOSFET

600 V, 7.4 A, 600 mΩ

### Features

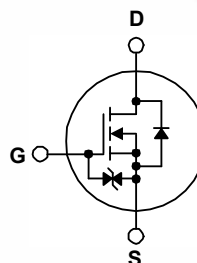
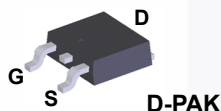
- 650 V @  $T_J = 150^\circ\text{C}$
- Typ.  $R_{DS(on)} = 510\text{ m}\Omega$
- Ultra Low Gate Charge (Typ.  $Q_g = 20\text{ nC}$ )
- Low Effective Output Capacitance (Typ.  $C_{oss(eff.)} = 74\text{ pF}$ )
- 100% Avalanche Tested
- ESD Improved Capacity
- RoHS Compliant

### Applications

- LCD / LED / PDP TV and Monitor Lighting
- Solar Inverter
- AC-DC Power Supply

### Description

SuperFET® II MOSFET is Fairchild Semiconductor's brand-new high voltage super-junction (SJ) MOSFET family that is utilizing charge balance technology for outstanding low on-resistance and lower gate charge performance. This technology is tailored to minimize conduction loss, provide superior switching performance, dv/dt rate and higher avalanche energy. Consequently, SuperFET II MOSFET is very suitable for the switching power applications such as PFC, server/telecom power, FPD TV power, ATX power and industrial power applications.



### Absolute Maximum Ratings $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	FCD600N60Z	Unit
$V_{DSS}$	Drain to Source Voltage	600	V
$V_{GSS}$	Gate to Source Voltage	- DC	±20
		- AC (f > 1 Hz)	±30
$I_D$	Drain Current	- Continuous ( $T_C = 25^\circ\text{C}$ )	7.4
		- Continuous ( $T_C = 100^\circ\text{C}$ )	4.7
$I_{DM}$	Drain Current	- Pulsed (Note 1)	22.2
$E_{AS}$	Single Pulsed Avalanche Energy	(Note 2)	135
$I_{AR}$	Avalanche Current	(Note 1)	1.5
$E_{AR}$	Repetitive Avalanche Energy	(Note 1)	0.89
dv/dt	MOSFET dv/dt	100	V/ns
	Peak Diode Recovery dv/dt (Note 3)	20	
$P_D$	Power Dissipation	( $T_C = 25^\circ\text{C}$ )	89
		- Derate Above $25^\circ\text{C}$	0.71
$T_J, T_{STG}$	Operating and Storage Temperature Range	-55 to +150	$^\circ\text{C}$
$T_L$	Maximum Lead Temperature for Soldering, 1/8" from Case for 5 Seconds	300	$^\circ\text{C}$

### Thermal Characteristics

Symbol	Parameter	FCD600N60Z	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	1.4	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	100	

## Package Marking and Ordering Information

Part Number	Top Mark	Package	Packing Method	Reel Size	Tape Width	Quantity
FCD600N60Z	FCD600N60Z	DPAK	Tape and Reel	330 mm	16 mm	2500 units

## Electrical Characteristics $T_C = 25^\circ\text{C}$ unless otherwise noted.

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 25^\circ\text{C}$	600	-	-	V
		$V_{GS} = 0\text{ V}, I_D = 10\text{ mA}, T_J = 150^\circ\text{C}$	650	-	-	
$\Delta BV_{DSS} / \Delta T_J$	Breakdown Voltage Temperature Coefficient	$I_D = 10\text{ mA}$ , Referenced to $25^\circ\text{C}$	-	0.67	-	$V/^\circ\text{C}$
$BV_{DS}$	Drain to Source Avalanche Breakdown Voltage	$V_{GS} = 0\text{ V}, I_D = 7.4\text{ A}$	-	700	-	V
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 480\text{ V}, V_{GS} = 0\text{ V}$	-	-	5	$\mu\text{A}$
		$V_{DS} = 480\text{ V}, T_C = 125^\circ\text{C}$	-	-	20	
$I_{GSS}$	Gate-Body Leakage Current	$V_{GS} = \pm 20\text{ V}, V_{DS} = 0\text{ V}$	-	-	$\pm 10$	$\mu\text{A}$

### On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 250\text{ }\mu\text{A}$	2.5	-	3.5	V
$R_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}, I_D = 3.7\text{ A}$	-	0.51	0.6	$\Omega$
$g_{FS}$	Forward Transconductance	$V_{DS} = 20\text{ V}, I_D = 3.7\text{ A}$	-	6.7	-	S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 25\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	840	1120	pF
$C_{oss}$	Output Capacitance		-	630	840	pF
$C_{rss}$	Reverse Transfer Capacitance		-	30	45	pF
$C_{oss}$	Output Capacitance	$V_{DS} = 380\text{ V}, V_{GS} = 0\text{ V}, f = 1\text{ MHz}$	-	16.5	-	pF
$C_{oss(eff.)}$	Effective Output Capacitance	$V_{DS} = 0\text{ V to } 480\text{ V}, V_{GS} = 0\text{ V}$	-	74	-	pF
$Q_{g(tot)}$	Total Gate Charge at 10V	$V_{DS} = 380\text{ V}, I_D = 3.7\text{ A}, V_{GS} = 10\text{ V}$ (Note 4)	-	20	26	nC
$Q_{gs}$	Gate to Source Gate Charge		-	3.4	-	nC
$Q_{gd}$	Gate to Drain "Miller" Charge		-	7.5	-	nC
ESR	Equivalent Series Resistance	$f = 1\text{ MHz}$	-	2.89	-	$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 380\text{ V}, I_D = 3.7\text{ A}, V_{GS} = 10\text{ V}, R_G = 4.7\text{ }\Omega$ (Note 4)	-	13	36	ns
$t_r$	Turn-On Rise Time		-	7	24	ns
$t_{d(off)}$	Turn-Off Delay Time		-	39	88	ns
$t_f$	Turn-Off Fall Time	(Note 4)	-	9	28	ns

### Drain-Source Diode Characteristics

I <sub>S</sub>	Maximum Continuous Drain to Source Diode Forward Current		-	-	7.4	A
I <sub>SM</sub>	Maximum Pulsed Drain to Source Diode Forward Current		-	-	22.2	A
V <sub>SD</sub>	Drain to Source Diode Forward Voltage	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3.7 A	-	-	1.2	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0 V, I <sub>SD</sub> = 3.7 A, dI <sub>F</sub> /dt = 100 A/μs	-	200	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge		-	2.3	-	μC

#### Notes:

1. Repetitive rating: pulse-width limited by maximum junction temperature.
2.  $I_{AS} = 1.5\text{ A}, V_{DD} = 50\text{ V}, R_G = 25\text{ }\Omega$ , starting  $T_J = 25^\circ\text{C}$ .
3.  $I_{SD} \leq 3.7\text{ A}, di/dt \leq 200\text{ A}/\mu\text{s}, V_{DD} \leq BV_{DSS}$ , starting  $T_J = 25^\circ\text{C}$ .
4. Essentially independent of operating temperature typical characteristics.

## Typical Performance Characteristics

Figure 1. On-Region Characteristics

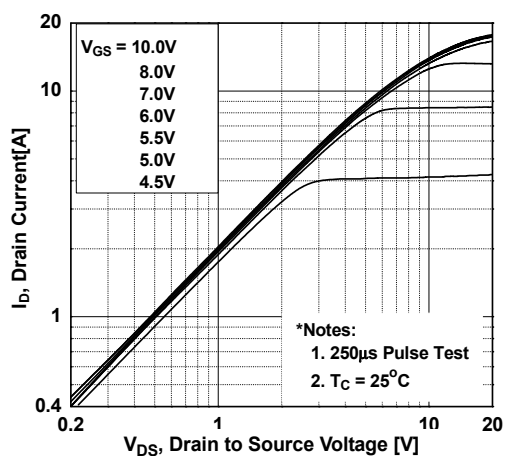


Figure 2. Transfer Characteristics

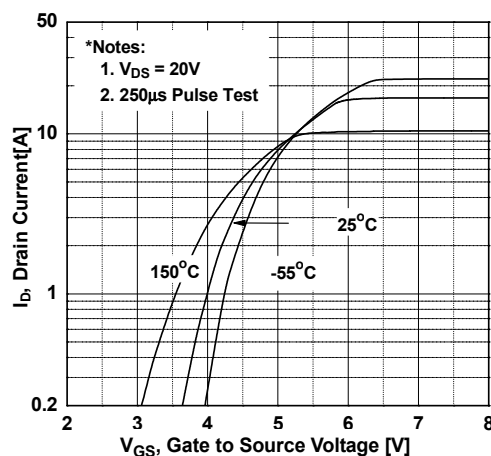


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

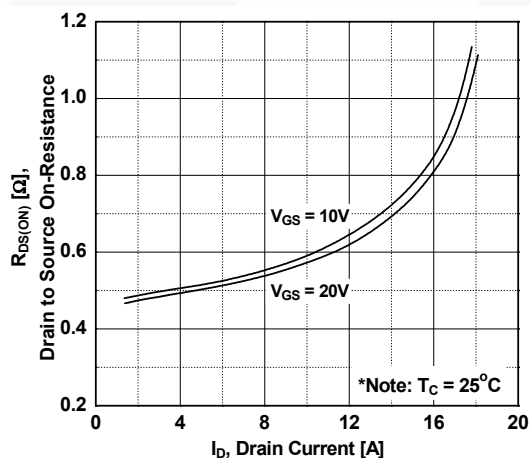


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

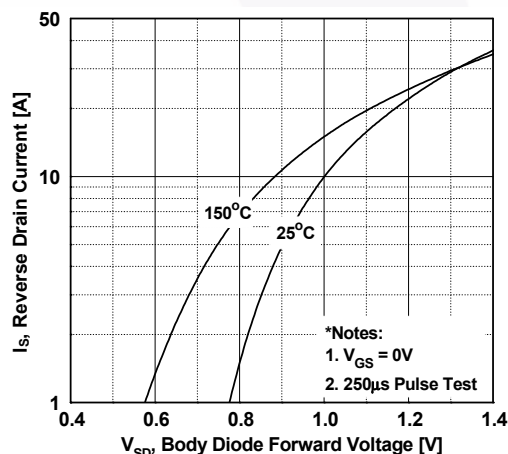


Figure 5. Capacitance Characteristics

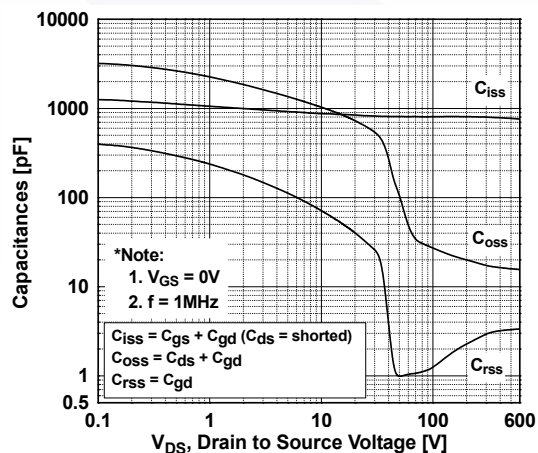
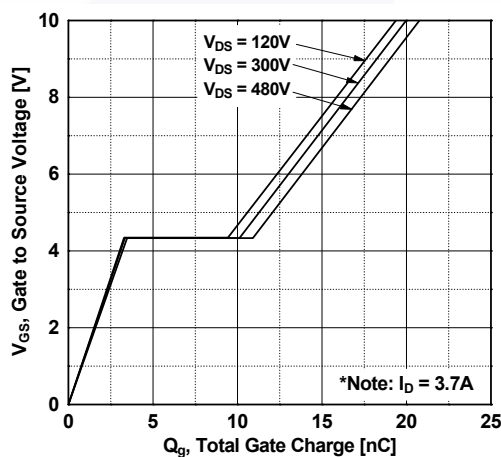


Figure 6. Gate Charge Characteristics



# Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

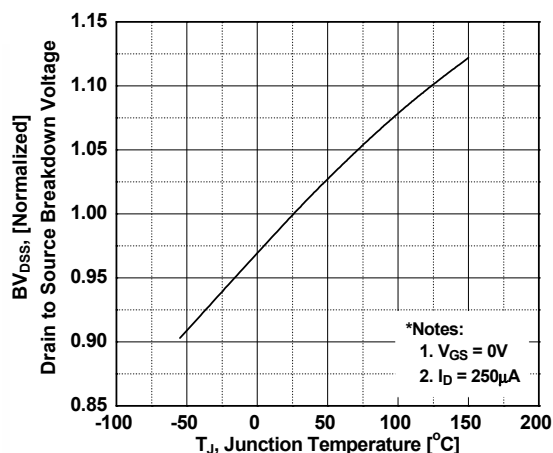


Figure 8. On-Resistance Variation vs. Temperature

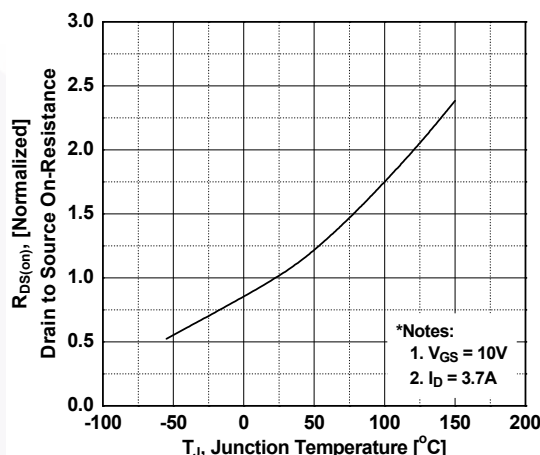


Figure 9. Maximum Safe Operating Area

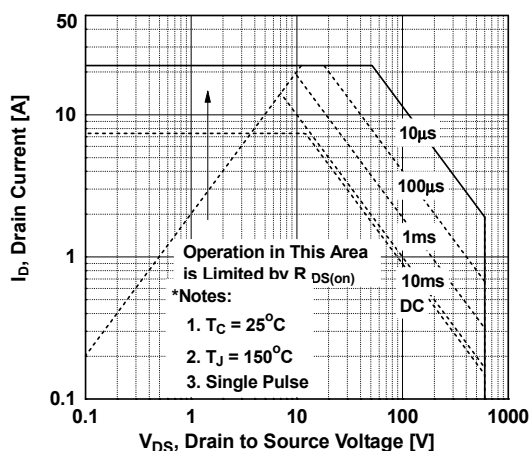


Figure 10. Maximum Drain Current vs. Case Temperature

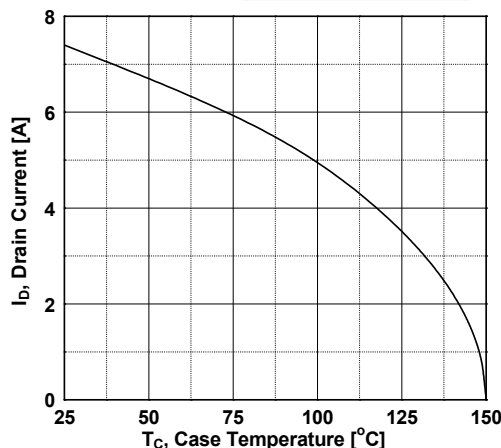
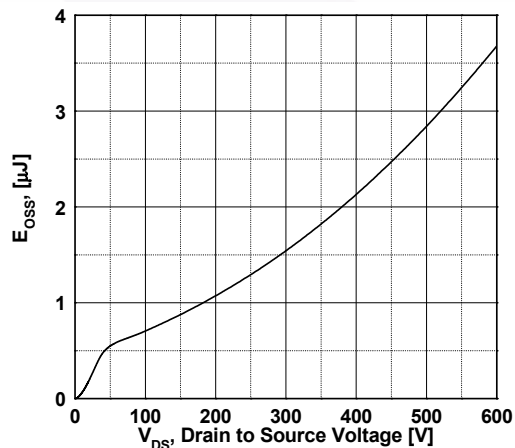
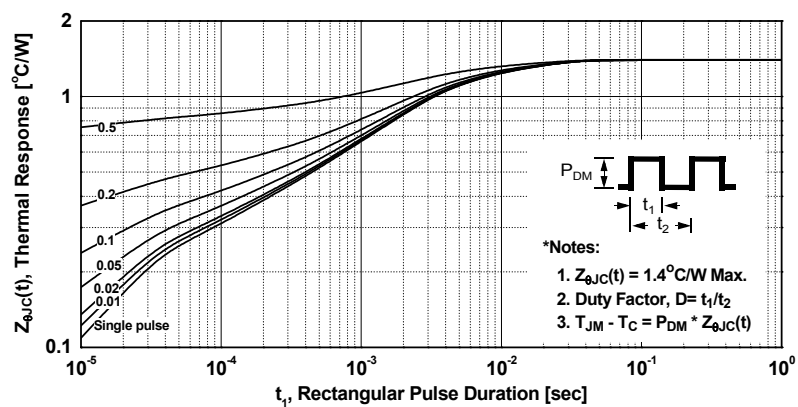


Figure 11. Eoss vs. Drain to Source Voltage



## Typical Performance Characteristics (Continued)

Figure 12. Transient Thermal Response Curve



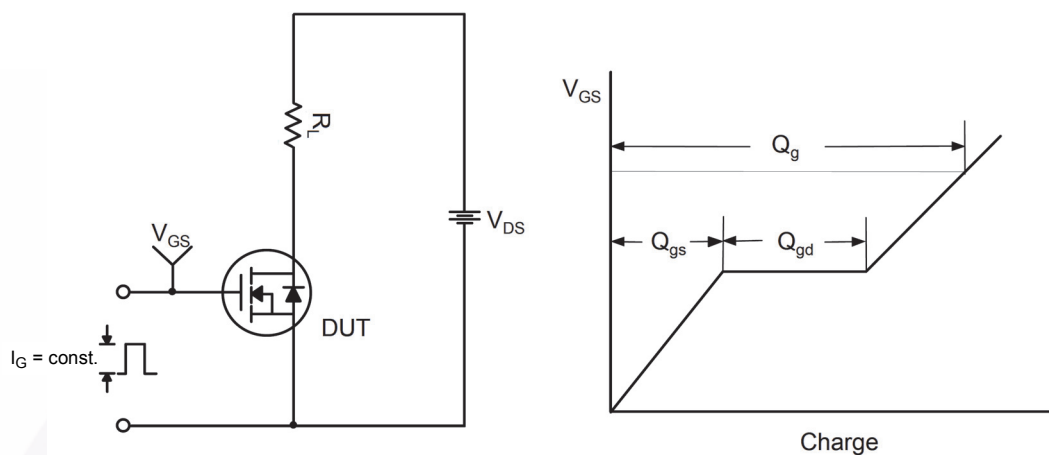


Figure 13. Gate Charge Test Circuit & Waveform

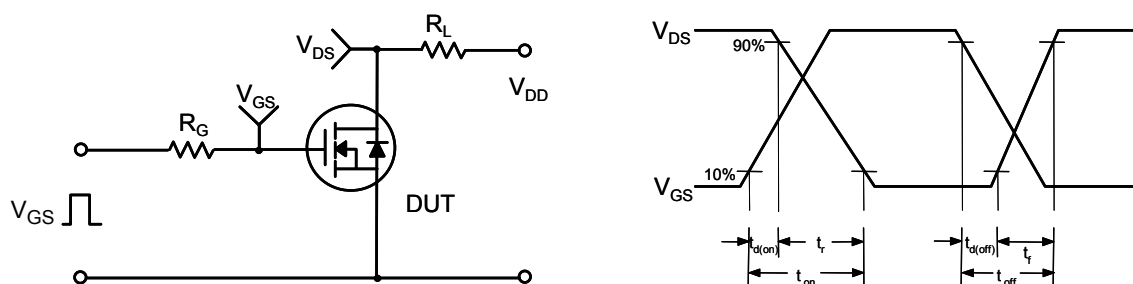


Figure 14. Resistive Switching Test Circuit & Waveforms

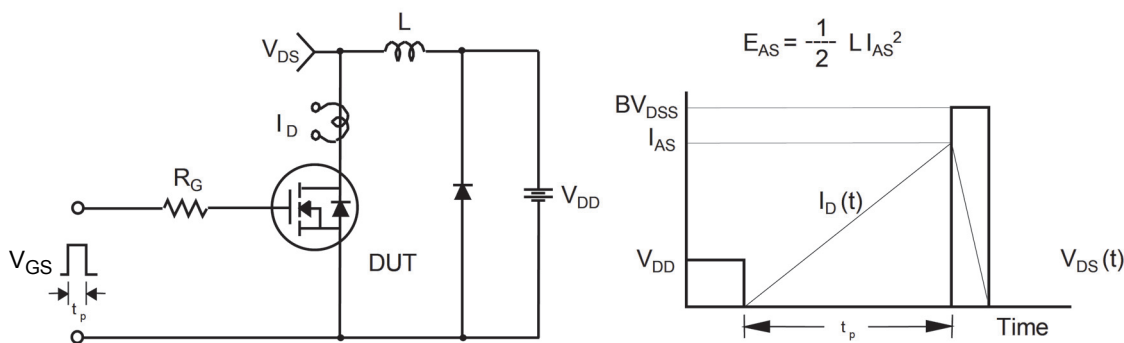


Figure 15. Unclamped Inductive Switching Test Circuit & Waveforms

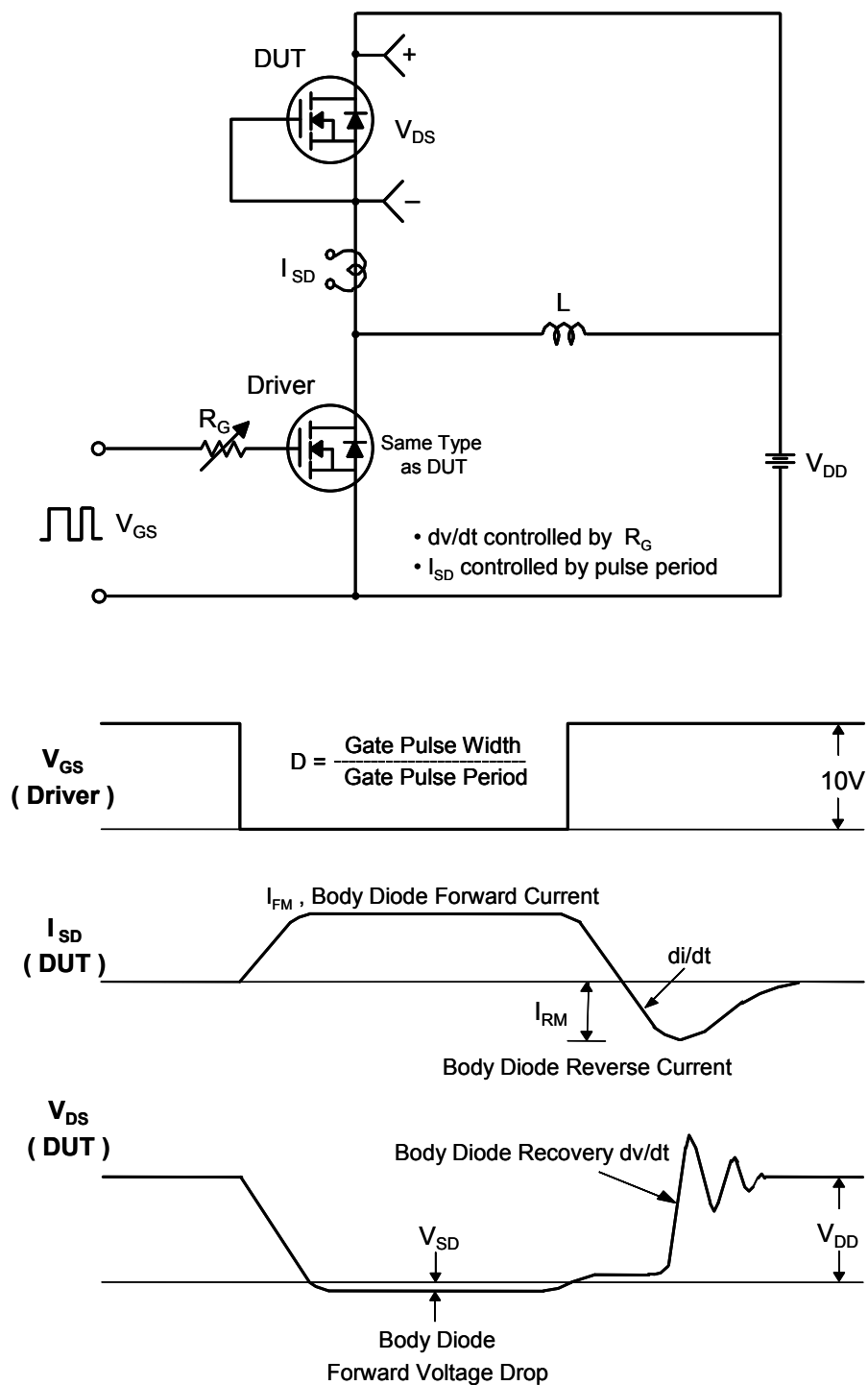
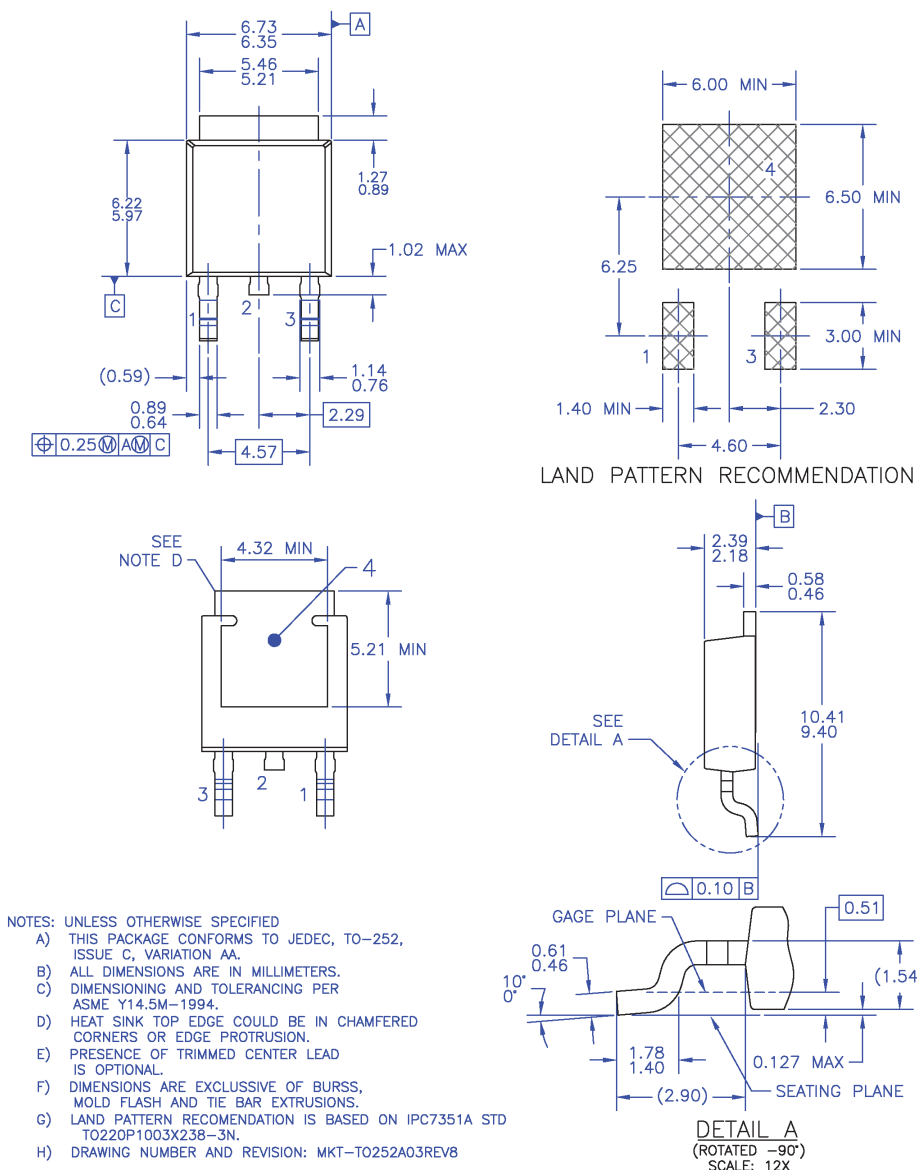


Figure 16. Peak Diode Recovery  $dv/dt$  Test Circuit & Waveforms



## Mechanical Dimensions



**Figure 17. TO252 (D-PAK), Molded, 3-Lead, Option AA&AB**

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